

PHASE-CHANGE MEMORY CELL AND
METHOD OF FABRICATING THE PHASE-CHANGE MEMORY CELL

ABSTRACT OF THE DISCLOSURE

A memory cell and method of fabricating the memory cell includes an insulating layer formed on a first electrode layer, the insulating layer having a first opening, a stencil layer formed on the insulating layer, and having a second opening formed in an area of the first opening, a phase-change material layer formed on a surface of the first electrode layer in the first opening, and an electrically conductive layer including a first portion formed on the stencil layer and defining a second electrode layer and a second portion formed on the phase-change material layer.